

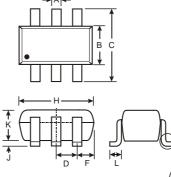


DMMT5551/DMMT5551S

MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DMMT5401)
- · Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, hfe, V_{CE(SAT)}, V_{BE(SAT)}
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)

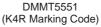


SOT-26 Max Dim Min Тур 0.35 0.50 0.38 В 1.60 1.50 1.70 С 2.70 3.00 2.80 D 0.95 F 0.55 Н 3.10 3.00 2.90 J 0.013 0.10 0.05 1.00 1.30 1.10 0.35 0.55 0.40 M 0.10 0.20 0.15 0° 8° All Dimensions in mm

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking (See Page 2): K4R & K4T
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)







DMMT5551S (K4T Marking Code)

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	180	V	
Collector-Emitter Voltage	V _{CEO}	160	V	
Emitter-Base Voltage	V _{EBO}	6.0	V	
Collector Current - Continuous (Note 2)	I _C	200	mA	
Power Dissipation (Note 2, 3)	P _d	300	mW	
Thermal Resistance, Junction to Ambient (Note 2)	R JA	417	°C/W	
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C	

Notes: 1. Built with adjacent die from a single wafer.

- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Maximum combined dissipation.
- No purposefully added lead.
- 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php..
- 6. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 7)									
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180		V	$I_C = 100 \mu A, I_E = 0$				
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160		V	$I_C = 1.0 \text{mA}, I_B = 0$				
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_E = 10 \mu A, I_C = 0$				
Collector Cutoff Current	I _{CBO}		50	nA μA	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C				
Emitter Cutoff Current	I _{EBO}		50	nA	V _{EB} = 4.0V, I _C = 0				
ON CHARACTERISTICS (Note 7)									
DC Current Gain (Note 8)	h _{FE}	80 80 30	250		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				
Collector-Emitter Saturation Voltage	V _{CE} (SAT)		0.15 0.20	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA				
Base-Emitter Saturation Voltage	V _{BE(SAT)}		1.0	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	Cobo		6.0	pF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_E = 0$				
Small Signal Current Gain	h _{FE}	50	250		V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz				
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz				
Noise Figure	NF		8.0	dB	$V_{CE} = 5.0V, I_{C} = 200\mu A,$ $R_{S} = 1.0k, f = 1.0kHz$				

Ordering Information (Note 6 & 9)

Device	Packaging	Shipping		
DMMT5551-7-F	SOT-26	3000/Tape & Reel		
DMMT5551S-7-F	SOT-26	3000/Tape & Reel		

Notes:

- Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. The DC Current Gain, h_{FE}, (matched at I_C = 10mA and V_{CE} = 5V) Collector Emitter Saturation Voltage, V_{CE(SAT)}, and Base Emitter Saturation Voltage, V_{BE(SAT)} are matched with typical matched tolerances of 1% and maximum of 2%.
- $9. \ \ \text{For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.}$

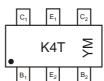
Marking Information



K4R = DMMT5551 Product Type Marking Code YM = Date Code Marking

Y = Year ex: T = 2006

M = Month ex: 9 = September



K4T = DMMT5551S Product Type Marking Code

YM = Date Code Marking

Y = Year ex: T = 2006

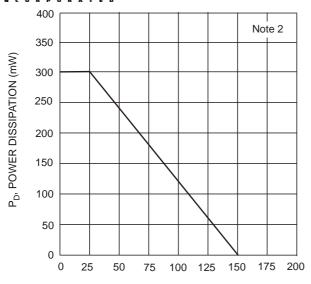
M = Month ex: 9 = September

Date Code Key

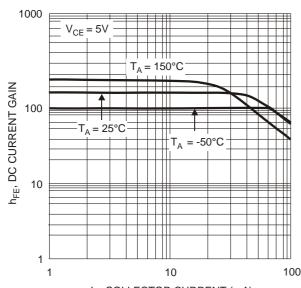
Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Q	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

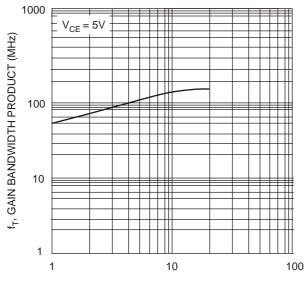
DIODES



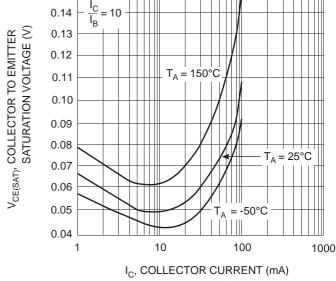
T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



I_C, COLLECTOR CURRENT (mA) Fig. 3, DC Current Gain vs Collector Current

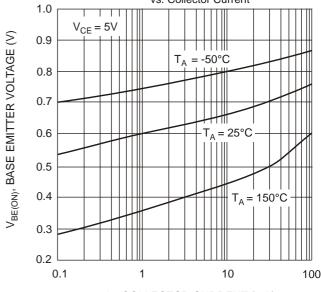


I_C, COLLECTOR CURRENT (mA) Fig. 5, Gain Bandwidth Product vs. Collector Current



0.15

Fig. 2, Collector Emitter Saturation Voltage
vs. Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 4, Base Emitter Voltage vs. Collector Current



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